Atomic Electrostatic Maps of 1D Channels in 2D Semiconductors using 4D Scanning Transmission

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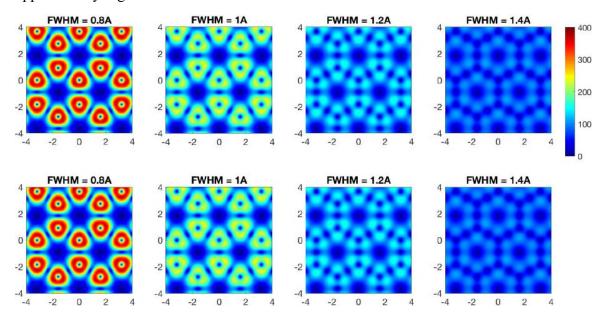
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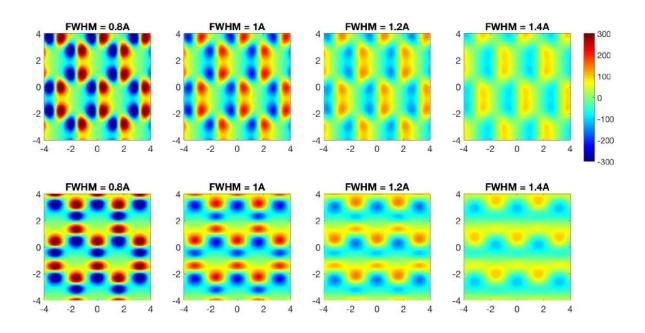
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Supplementary Information

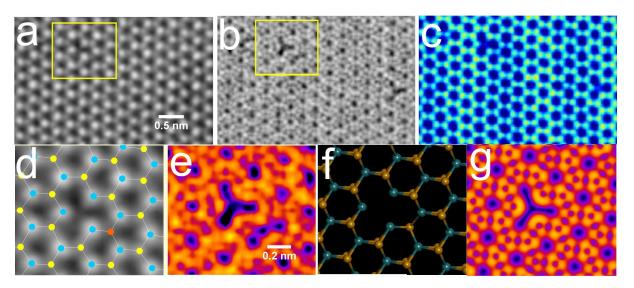
Supplementary Figures



Supplementary figure 1. MoS_2 pristine monolayer crystal: integrated electric field $\tilde{E}^{\sigma}(\vec{r})$ calculated from pseudo-potential DFT (upper figures) and all-electron DFT (lower figures) with varying FWHM (from 0.8Å to 1.5Å) for gaussian smearing. The unit is in volt.

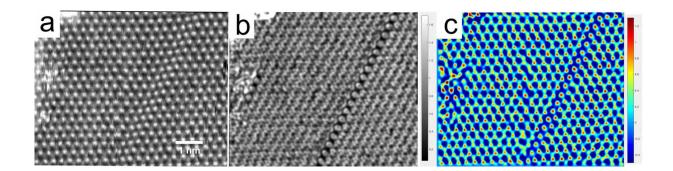


Supplementary figure 2: MoS₂ pristine monolayer crystal: integrated electric field $\tilde{E}_x^{\sigma}(\vec{r})$ (upper figures) and $\tilde{E}_y^{\sigma}(\vec{r})$ (lower figures) with varying FWHM (from 0.8Å to 1.4Å) for gaussian smearing. The unit is in volt.

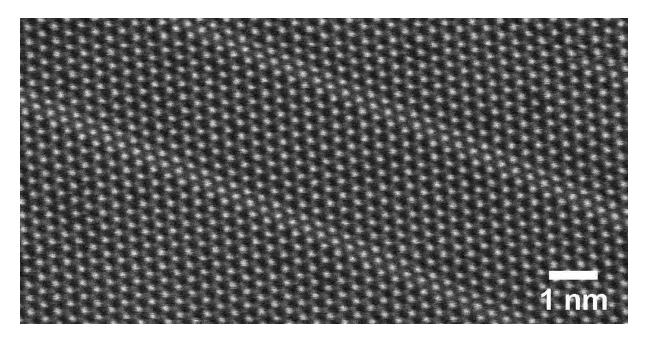


Supplementary figure 3. 4D STEM of S point vacancies in MoS_2 . (a) LAADF image reconstructed from the 4D STEM data. (b) Experimental $|E\perp|$ around MoS_2 reconstructed from the 4D STEM

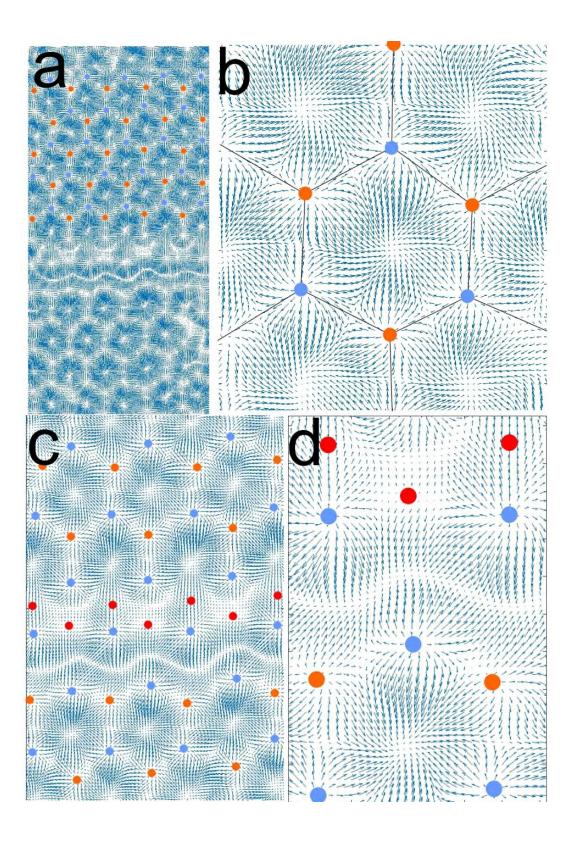
data, using the modulus of I_{com} , normalized and scaled to match the DFT data range. (c) Ptychographic phase of the same area reconstructed from the 4D STEM data. (d) Magnified view from the yellow box in (a). Orange spot indicates 1S vacancy position. (e) Magnified view of the yellow box in (b), with a colour LUT (Fire). (f) Atomic model of 2S point vacancy. (g) DFT calculated $|E\perp|$ map around a 2S defect in MoS_2 .



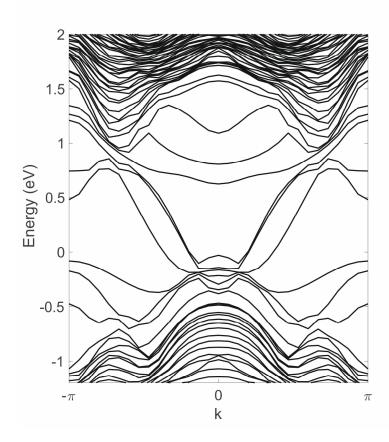
Supplementary figure 4. 4D STEM data of 2S line vacancy in WS₂. (a) (a) LAADF image reconstructed from the 4D STEM data. (b) Experimental $|E\perp|$ around WS₂ reconstructed from the 4D STEM data, using the modulus of I_{com} , normalized and scaled to match the DFT data range. (c) Total charge image reconstructed from the 4D STEM data. Colour LUT used.



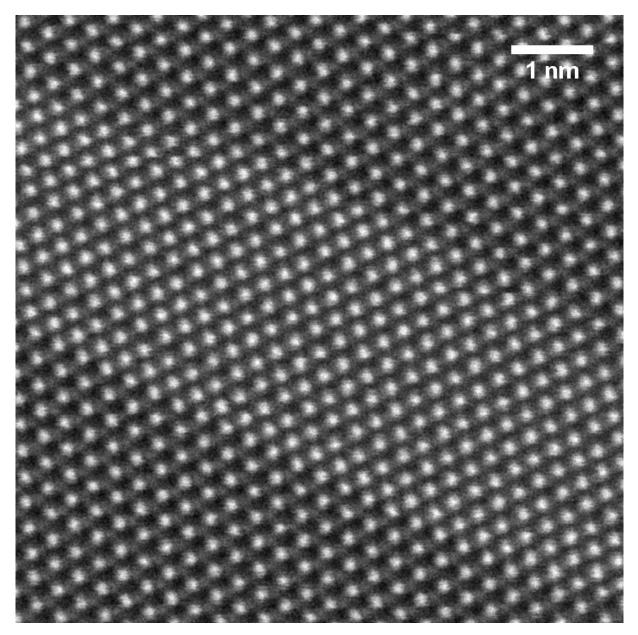
Supplementary figure 5. ADF-STEM image of two isolated ultralong S line vacancines in WS_2 .



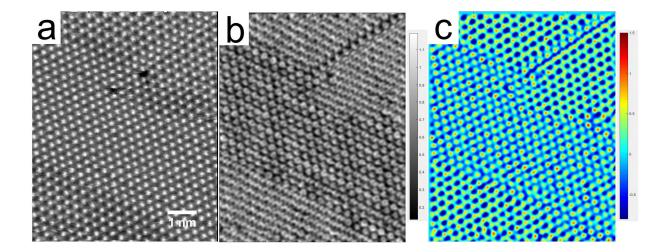
Supplementary figure 6. (a) Vector map of E^{\perp} around a line vacancy in MoS_2 . (b) Higher magnification map of a pristine area. (c) Higher magnification image of the line defect area. (d) Higher magnification image of the 1D channel.



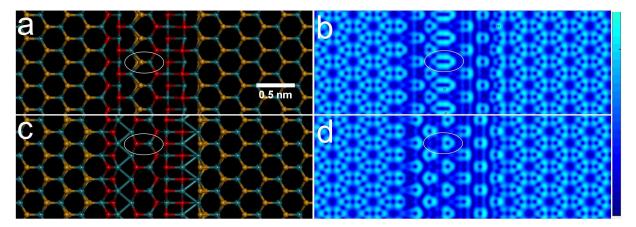
Supplementary figure 7. DFT calculated band structure of in-gap states for a 2SVL line vacancy in WS_2 .



Supplementary figure 8. ADF-STEM image recorded with a long scan dwell time (32 μs per pixel) of a complex line vacancy regions in WS₂ at 800°C.



Supplementary figure 9. 4D STEM data of dense vacancy area in WS₂. (a) LAADF image reconstructed from the 4D STEM data. (b) Experimental $|E\perp|$ around WS₂ reconstructed from the 4D STEM data, using the modulus of I_{com} , normalized and scaled to match the DFT data range. (c) Total charge image reconstructed from the 4D STEM data. Colour LUT used.



Supplementary figure 10. Comparison of DFT calculated $|E\perp|$ in MoS₂ for two slightly different defect structures in MoS₂. (a) and (c) are atomic models and (b),(d) the respective DFT calculations. White oval indicates region where number of S atoms changes. Red atoms indicate 1S sites, due to S vacancies. Orange atoms are S in 2S sites and blue atoms are Mo.

Supplementary Note 1

The following matlab code shows the implementation of computing the FFT component with smearing.

```
%MATLAB code for DFT using 1.2 sigma smearing.
%% define constants
ep0=8.854187817E-12; % F/m
echarge=1.6E-19; % C
AAunit=1E-10;
EF_convert=echarge*(1/(AAunit^2))/ep0/(1/AAunit);
%% compute the FFT component with smearing
EF_smear_fft=zeros(num_hex,2);
valence CHARGE smear fft=zeros(num hex,1);
total CHARGE smear fft=zeros(num hex,1);
beam sigma constant=1/2/sqrt(2*log(2));
beam sigma=(1.2)*beam sigma constant;
for indh=1:num hex
    indh
    bvec now=hex list(indh,:);
    total rho fft=total charge fft(indh);
    nbvec now=bvec now/sqrt(dot(bvec now,bvec now));
    qauss fac=exp(-dot(bvec now,bvec now)*beam sigma*beam sigma/2);
    EF smear_fft(indh,1:2)=-
i*total rho fft*nbvec now/sqrt(dot(bvec now,bvec now))*gauss fac;
    valence CHARGE smear fft(indh) = -valence charge fft(indh) * gauss fac;
    total CHARGE smear fft(indh)=total charge fft(indh)*gauss fac;
%% Fourier transform back to real space for the charge and electric field
(smeared)
num1=1000;
num2=100;
dis x=linspace(0,42,num1)+all atom pos shift(1);
dis y=linspace(-7,7,num2)+all atom pos shift(2);
[disp xx,disp yy]=meshgrid(dis x,dis y);
smear EF=zeros(num2, num1, 2);
smear_valence_charge=zeros(num2,num1);
smear total charge=zeros(num2, num1);
for indh=1:num_hex
    indh
    bvec now=hex list(indh,:);
    tmpexp=exp(i*(disp xx*bvec now(1)+disp yy*bvec now(2)));
```

```
smear_EF(:,:,1)=smear_EF(:,:,1)+EF_smear_fft(indh,1)*tmpexp;
smear_EF(:,:,2)=smear_EF(:,:,2)+EF_smear_fft(indh,2)*tmpexp;

smear_valence_charge(:,:)=smear_valence_charge(:,:)+valence_CHARGE_smear_fft(indh)*tmpexp;

smear_total_charge(:,:)=smear_total_charge(:,:)+total_CHARGE_smear_fft(indh)*tmpexp;
end

smear_valence_charge=smear_valence_charge-valence_charge_fft(num_hex+1);

smear_EF=real(smear_EF)*EF_convert;
smear_valence_charge=real(smear_valence_charge);
smear_total_charge=real(smear_total_charge);
```